



300W 808nm High-power Laser Chip Bare Chips not bonded on Submount

Application:

Semiconductors for **military ranging radar**

Semiconductors as **pumping sources for solid-state lasers**.

Use in printing technology. Esthetics, dermatology and surgery.

Data Sheet

Item No: LC808SB300

Item Name: High-power Industrial Laser Chips 300W 808nm

Operation

Center Wavelength	808nm
Output Power	300W
Operation Mode	QCW
Power modulation	100%

Geometrical

Numbers of Emitters	60
Emitter width	120um
Cavity length	1500um
Emitter Pitch	160um
Filling factor	75%
Bar width	10000um
Thickness	125um

Electro Optical Data

Threshold current	30A
Operating current	280-290A
Operating voltage	1.9-2.1V
Pulse wavelength	803nm
Conversion efficiency	50%
Slope efficiency	1.2W/A
Slow axis divergence	12
Fast axis divergence	39
Spectral width	4nm
Temperature characteristics	0.28nm/°C
Polarization	TE
LD operating temperature	25°C